

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S85	50	(anneal\$ or heat\$3 near2 treat\$4 or rta or rtp or ptp) same (Si or silicon ) near4 wafer same (low or slow or reduc\$4) near2 rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 15:12
S17	123	wafer and (anneal\$3 or (heat adj treat\$4) or (rapid adj thermal) or RTA or RTP or PTP) same temperature and czochralski and ((defect adj free) or perfect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 15:12
L2	50	(anneal\$ or heat\$3 near2 treat\$4 or rta or rtp or ptp) same (Si or silicon ) near4 wafer same (low or slow or reduc\$4) near2 rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 15:12
L1	300	wafer and (anneal\$3 or (heat adj treat\$4) or (rapid adj thermal) or RTA or RTP or PTP) same temperature and czochralski and ((defect adj free) or perfect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 15:12
S75	301402	(koso near2 nakamura or toshiaki near2 saishoji or hirotaka near2 nakajima or masashi near2 kotooka or yoshiyuki near2 shimanuki).in. or (KOMATSU DENSHI KINZOKU KABUSHIKI KAISHA).as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 15:13
L5	0	3 same heat near2 treat\$6 same Czochralski	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 15:13
L4	0	3 same heat near2 treat\$6 same Czochralski same wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 15:13
L3	311704	(koso near2 nakamura or toshiaki near2 saishoji or hirotaka near2 nakajima or masashi near2 kotooka or yoshiyuki near2 shimanuki).in. or (KOMATSU DENSHI KINZOKU KABUSHIKI KAISHA).as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 15:13
L7	30	3 and heat near2 treat\$6 same Czochralski same wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 15:14

L6	46	3 and heat near2 treat\$6 same Czochralski	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 15:14
S86	121	heat near2 treat\$4 near10 temperature near10 (ramp\$4 or rate) same (si or silicon) near5 (single near2 crystal\$5 or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 15:15
S15	82	wafer and (anneal\$3 or (heat adj treat\$4) or (rapid adj thermal) or RTA or RTP or PTP) same temperature and czochralski and (oxygen or O2) and (oSF or OSIF or BMD or (oxide adj induced))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 15:15
L9	129	heat near2 treat\$4 near10 temperature near10 (ramp\$4 or rate) same (si or silicon) near5 (single near2 crystal\$5 or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 15:15
L8	205	wafer and (anneal\$3 or (heat adj treat\$4) or (rapid adj thermal) or RTA or RTP or PTP) same temperature and czochralski and (oxygen or O2) and (oSF or OSIF or BMD or (oxide adj induced))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/15 15:15